



SCT2280KEC Information



For Reference Only

Part Number SCT2280KEC

Manufacturer Rohm Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 14A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









SCT2280KEC Specifications

Manufacturer Part Number SCT2280KEC Manufacturer Rohm Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs 36nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 667pF @ 800V Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology SiCFET (Silicon Carbide) Toain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 18HV Input Capacitance (Ciss) (Max) @ Vds 667pF @ 800V Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Supplier Device Package TO-247- Package / Case TO-247-3	Manufacturer Part Number	SCT2280KEC
Package TO-247-3 Series - FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs 36nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 667pF @ 800V Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Manufacturer	Rohm Semiconductor
PackageTO-247-3Series-FET TypeN-ChannelTechnologySiCFET (Silicon Carbide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)18VVgs(th) (Max) @ Id4V @ 1.4mAGate Charge (Qg) (Max) @ Vgs36nC @ 18VInput Capacitance (Ciss) (Max) @ Vds667pF @ 800VVgs (Max)+22V, -6VFET Feature-Power Dissipation (Max)108W (Tc)Rds On (Max) @ Id, Vgs364 mOhm @ 4A, 18VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologySiCFET (Silicon Carbide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)18VVgs(th) (Max) @ Id4V @ 1.4mAGate Charge (Qg) (Max) @ Vgs36nC @ 18VInput Capacitance (Ciss) (Max) @ Vds667pF @ 800VVgs (Max)+22V, -6VFET Feature-Power Dissipation (Max)108W (Tc)Rds On (Max) @ Id, Vgs364 mOhm @ 4A, 18VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology SiCFET (Silicon Carbide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs 36nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 667pF @ 800V Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package 70-247 Package / Case 71-25C (TJ)	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package TO-247-3	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 14A (Tc) 14A (Tc) 14A (Tc) 14A (Tc) 14A (Tc) 14B (Tc) 18V 4V @ 1.4mA 6667pF @ 800V +22V, -6V -22V, -6V -21V, -6V TO-247 Through Hole	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 18V Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) 422V, -6V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247- Package / Case 14A (Tc) 14V 14A (Tc) 16V 16V 16V 16T 17D 18V 16T 17D 18V 16T 17D 18V 17D 18V 18V 10S 10S 10S 10S 10S 10S 10S 10	Technology	SiCFET (Silicon Carbide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) +22V, -6V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id 4V @ 1.4mA Gate Charge (Qg) (Max) @ Vgs 36nC @ 18V Input Capacitance (Ciss) (Max) @ Vds 667pF @ 800V Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	14A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 667pF @ 800V Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	18V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Vgs(th) (Max) @ Id	4V @ 1.4mA
Vgs (Max) +22V, -6V FET Feature - Power Dissipation (Max) 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Gate Charge (Qg) (Max) @ Vgs	36nC @ 18V
FET Feature - 108W (Tc) Rds On (Max) @ Id, Vgs 364 mOhm @ 4A, 18V Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	667pF @ 800V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case 108W (Tc) 364 mOhm @ 4A, 18V Through Hole Through Hole TO-247-3	Vgs (Max)	+22V, -6V
Rds On (Max) @ Id, Vgs364 mOhm @ 4A, 18VOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247Package / CaseTO-247-3	FET Feature	-
Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Power Dissipation (Max)	108W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	364 mOhm @ 4A, 18V
Supplier Device Package TO-247 Package / Case TO-247-3	Operating Temperature	175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247
Report errors?	Package / Case	TO-247-3
		Report errors?

SCT2280KEC Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SCT2280KEC Payment Methods



















SCT2280KEC Shipping Methods













If you have any question about SCT2280KEC, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com